

#### **Features**

- Trench Power LV MOSFET Technology
- · Excellent Package for Heat Dissipation
- High Density Cell Desihn for Low R<sub>DS(on)</sub>
- · Epoxy Meets UL 94 V-0 Flammability Rating
- · Moisture Sensitivity Level 1
- · Halogen Free Available Upon Request By Adding Suffix "-HF"
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

## **Maximum Ratings**

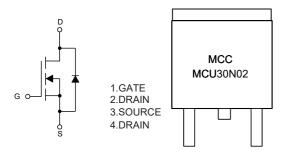
- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance: 5°C/W Junction to Case (Note 1)

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V <sub>DS</sub>	20	<b>V</b>	
Gate-Source Volltage	V <sub>GS</sub>	±10	V	
Continuous Drain Current	T <sub>C</sub> =25°C	1	30	Α
	T <sub>C</sub> =100°C	l <sub>D</sub>	21	Α
Pulsed Drain Current (Note 2	I <sub>DM</sub>	125	Α	
Single Pulse Avalanche E	E <sub>AS</sub>	100	mJ	
Total Power Dissipation	T <sub>C</sub> =25°C	P <sub>D</sub>	30	W
	T <sub>C</sub> =100°C	] 'D	15	W

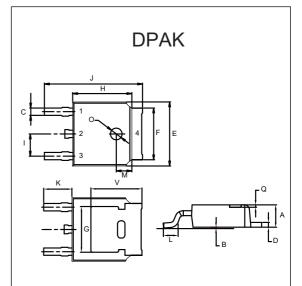
#### Note:

- $1.R_{\theta,JA}$  is the Sum of the Junction-to-Case and Case-to-Ambient Thermal Resistance, Where the Case Thermal Reference is Defined as the Solder Mounting Surface of the Drain Pins.  $R_{\theta,JC}$  is Guaranteed by Design, While  $R_{\theta,JA}$  is Determined by the Board Design. The Maximum Rating Presented Here is Based on Mounting on a 1 in  $^2$  Pad of 2oz Copper.
- 2.Pulse Test: Pulse Width $\leq$ 300 $\mu$ s,Duty Cycle  $\leq$ 2%.
- $3.T_J = 25$ °C,  $V_{DD} = 20V$ ,  $V_G = 10V$ , L = 0.5mH,  $R_q = 25\Omega$

## ±bh/fbU Ghfi Wi fY UbX A Uf\_]b[ '7 cXY



# N-CHANNEL MOSFET



DIMENSIONS					
DIM	INCHES		MM		NOTE
DIIVI	MIN	MAX	MIN	MAX	NOTE
Α	0.087	0.094	2.20	2.40	
В	0.000	0.005	0.00	0.13	
С	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
Е	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
Н	0.236	0.244	6.00	6.20	
I	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.055	0.067	1.40	1.70	
М	0.063		1.60		TYP.
0	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.35		TYP.

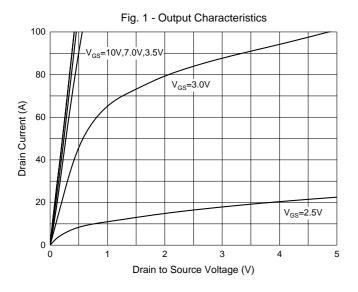


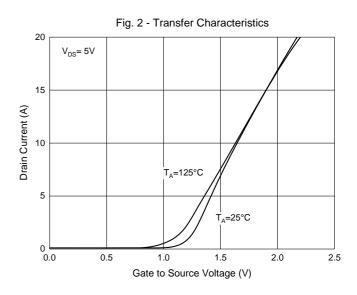
# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

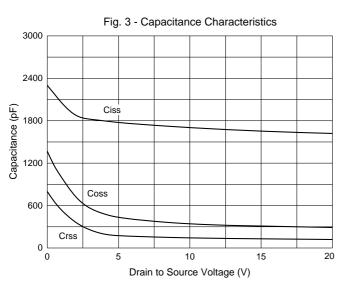
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics					1	1	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±10V			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	0.45	0.62	1	V	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A		5.6	7	mΩ	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =7A		7.1	9		
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =3A		10	14		
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =15A		0.9	1.2	V	
Continuous Body Diode Current	Is				30	Α	
Dynamic Characteristics							
Input Capacitance	C <sub>iss</sub>			1700		pF	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =10V,V <sub>GS</sub> =0V,f=1MHz		305			
Reverse Transfer Capacitance	C <sub>rss</sub>			145			
Total Gate Charge	$Q_g$			29			
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =10V,V <sub>GS</sub> =4.5V,I <sub>D</sub> =15A		6		nC	
Gate-Drain Charge	$Q_{gd}$			7			
Reverse Recovery Chrage	Q <sub>rr</sub>	1 -15A di/dt-100A/us		23			
Reverse Recovery Time	t <sub>rr</sub>	I <sub>S</sub> =15A, di/dt=100A/μs		39			
Turn-On Delay Time	t <sub>d(on)</sub>			7			
Turn-On Rise Time	t <sub>r</sub>	V <sub>GS</sub> =4.5V,V <sub>DD</sub> =10V, I <sub>D</sub> =10A,		35		ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_L=1\Omega,R_{GEN}=3\Omega$		30			
Turn-Off Fall Time	t <sub>f</sub>			6			

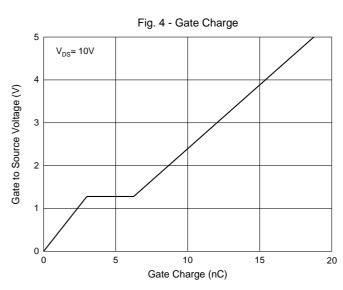


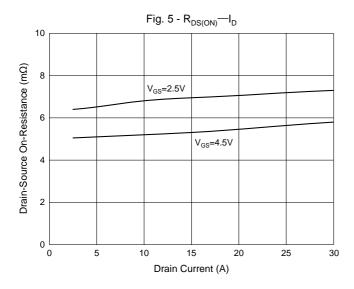
### **Curve Characteristics**

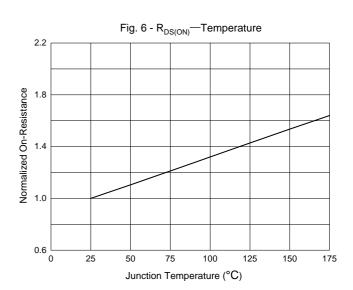














## **Ordering Information**

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel

Note: Adding "-HF" Suffix for Halogen Free, eg. Part Number-TP-HF

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